

## Features

- Very high speed: 45 ns
- Wide voltage range: 2.2 V to 3.6 V and 4.5 V to 5.5 V
- Ultra low standby power
  - Typical standby current: 1  $\mu$ A
  - Maximum standby current: 4  $\mu$ A
- Ultra low active power
  - Typical active current: 1.3 mA at f = 1 MHz
- Easy memory expansion with  $\overline{CE}$ , and  $\overline{OE}$  features
- Automatic power down when deselected
- Complementary metal oxide semiconductor (CMOS) for optimum speed and power
- Available in Pb-free 44-pin thin small outline package (TSOP) Type II package

## Functional Description

The CY62126ESL is a high performance CMOS static RAM organized as 64K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications. The device also has an automatic power down feature that significantly reduces power consumption when

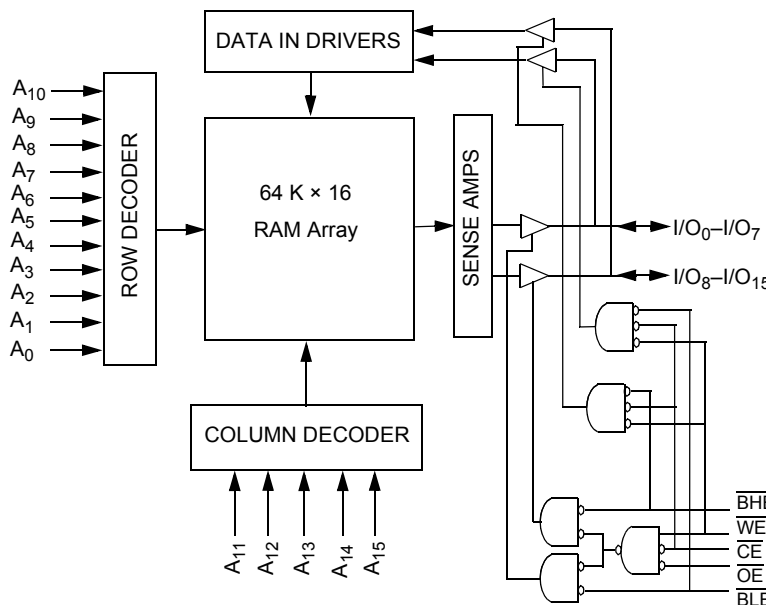
addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99 percent when deselected ( $\overline{CE}$  HIGH). The input and output pins ( $I/O_0$  through  $I/O_{15}$ ) are placed in a high impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), both Byte High Enable and Byte Low Enable are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH) or during a write operation ( $\overline{CE}$  LOW and  $\overline{WE}$  LOW).

To write to the device, take Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from  $I/O$  pins ( $I/O_0$  through  $I/O_7$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{15}$ ). If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from  $I/O$  pins ( $I/O_8$  through  $I/O_{15}$ ) is written into the location specified on the address pins ( $A_0$  through  $A_{15}$ ).

To read from the device, take Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte Low Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins appear on  $I/O_0$  to  $I/O_7$ . If Byte High Enable ( $\overline{BHE}$ ) is LOW, then data from memory appears on  $I/O_8$  to  $I/O_{15}$ . See the Truth Table on page 11 for a complete description of read and write modes.

The CY62126ESL device is suitable for interfacing with processors that have TTL I/P levels. It is not suitable for processors that require CMOS I/P levels. Please see Electrical Characteristics on page 4 for more details and suggested alternatives.

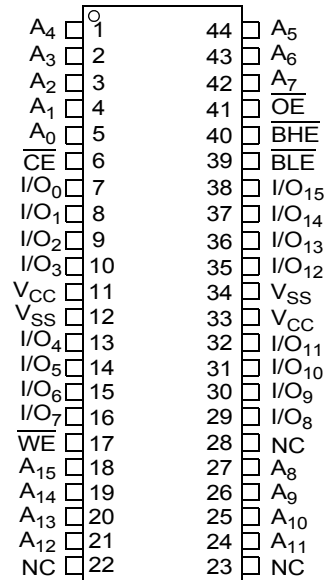
## Logic Block Diagram



## Contents

<b>Pin Configuration</b> .....	<b>3</b>	<b>Truth Table</b> .....	<b>11</b>
<b>Product Portfolio</b> .....	<b>3</b>	<b>Ordering Information</b> .....	<b>12</b>
<b>Maximum Ratings</b> .....	<b>4</b>	Ordering Code Definitions .....	12
<b>Operating Range</b> .....	<b>4</b>	<b>Package Diagram</b> .....	<b>13</b>
<b>Electrical Characteristics</b> .....	<b>4</b>	<b>Acronyms</b> .....	<b>14</b>
<b>Capacitance</b> .....	<b>5</b>	<b>Document Conventions</b> .....	<b>14</b>
<b>Thermal Resistance</b> .....	<b>5</b>	Units of Measure .....	14
<b>AC Test Loads and Waveforms</b> .....	<b>5</b>	<b>Document History Page</b> .....	<b>15</b>
<b>Data Retention Characteristics</b> .....	<b>6</b>	<b>Sales, Solutions, and Legal Information</b> .....	<b>16</b>
<b>Data Retention Waveform</b> .....	<b>6</b>	Worldwide Sales and Design Support .....	16
<b>Switching Characteristics</b> .....	<b>7</b>	Products .....	16
<b>Switching Waveforms</b> .....	<b>8</b>	PSoC Solutions .....	16

## Pin Configuration

**44-pin TSOP II (Top View) [1]**


## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V) [2]	Speed (ns)	Power Dissipation					
				Operating I <sub>CC</sub> (mA)				Standby, I <sub>SB2</sub> (μA)	
				f = 1MHz		f = f <sub>max</sub>			
				Typ [3]	Max	Typ [3]	Max	Typ [3]	Max
CY62126ESL	Industrial	2.2 V–3.6 V and 4.5 V–5.5 V	45	1.3	2	11	16	1	4

**Notes**

1. NC pins are not connected on the die.
2. Datasheet specifications are not guaranteed for V<sub>CC</sub> in the range of 3.6 V to 4.5 V.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.

## Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature .....	-65 °C to +150 °C
Ambient temperature with power applied .....	55 °C to +125 °C
Supply voltage to ground potential .....	-0.5 V to 6.0 V
DC voltage applied to outputs in High Z State <sup>[4, 5]</sup> .....	-0.5 V to 6.0 V
DC input voltage <sup>[4, 5]</sup> .....	-0.5 V to 6.0 V

Output current into outputs (low) .....	20 mA
Static discharge voltage (MIL-STD-883, Method 3015) .....	> 2001 V
Latch up current .....	> 200 mA

## Operating Range

Device	Range	Ambient Temperature	V <sub>CC</sub> <sup>[6]</sup>
CY62126ESL	Industrial	-40 °C to +85 °C	2.2 V–3.6 V, and 4.5 V–5.5 V

## Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		45 ns			Unit
				Min	Typ <sup>[7]</sup>	Max	
V <sub>OH</sub>	Output high voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7	I <sub>OH</sub> = -0.1 mA	2.0	-	-	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6	I <sub>OH</sub> = -1.0 mA	2.4	-	-	
		4.5 ≤ V <sub>CC</sub> ≤ 5.5	I <sub>OH</sub> = -1.0 mA	2.4	-	-	
		4.5 ≤ V <sub>CC</sub> ≤ 5.5	I <sub>OH</sub> = -0.1 mA	-	-	3.4 <sup>[8]</sup>	
V <sub>OL</sub>	Output low voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7	I <sub>OL</sub> = 0.1 mA	-	-	0.4	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6	I <sub>OL</sub> = 2.1 mA	-	-	0.4	
		4.5 ≤ V <sub>CC</sub> ≤ 5.5	I <sub>OL</sub> = 2.1 mA	-	-	0.4	
V <sub>IH</sub>	Input high voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7		1.8	-	V <sub>CC</sub> + 0.3	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6		2.2	-	V <sub>CC</sub> + 0.3	
		4.5 ≤ V <sub>CC</sub> ≤ 5.5		2.2	-	V <sub>CC</sub> + 0.5	
V <sub>IL</sub>	Input low voltage	2.2 ≤ V <sub>CC</sub> ≤ 2.7		-0.3	-	0.6	V
		2.7 ≤ V <sub>CC</sub> ≤ 3.6		-0.3	-	0.8	
		4.5 ≤ V <sub>CC</sub> ≤ 5.5		-0.5	-	0.8	
I <sub>IX</sub>	Input leakage current	GND ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>		-1	-	+1	μA
I <sub>OZ</sub>	Output leakage current	GND ≤ V <sub>O</sub> ≤ V <sub>CC</sub> , Output disabled		-1	-	+1	μA
I <sub>CC</sub>	V <sub>CC</sub> operating supply current	f = f <sub>max</sub> = 1/t <sub>RC</sub>	V <sub>CC</sub> = V <sub>CCmax</sub>	-	11	16	mA
		f = 1 MHz	I <sub>OUT</sub> = 0 mA, CMOS levels	-	1.3	2.0	
I <sub>SB1</sub> <sup>[9]</sup>	Automatic CE power down current – CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2 \text{ V}$ , V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.2 V or V <sub>IN</sub> ≤ 0.2 V, f = f <sub>max</sub> (address and data only), f = 0 ( $\overline{OE}$ and $\overline{WE}$ ), V <sub>CC</sub> = V <sub>CC(max)</sub>		-	1	4	μA
I <sub>SB2</sub> <sup>[9]</sup>	Automatic CE power down current – CMOS inputs	$\overline{CE} \geq V_{CC} - 0.2 \text{ V}$ , V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.2 V or V <sub>IN</sub> ≤ 0.2 V, f = 0, V <sub>CC</sub> = V <sub>CC(max)</sub>		-	1	4	μA

### Notes

- V<sub>IL(min)</sub> = -2.0 V for pulse durations less than 20 ns.
- V<sub>IH(max)</sub> = V<sub>CC</sub> + 0.75 V for pulse durations less than 20 ns.
- Full device AC operation assumes a minimum of 100 μs ramp time from 0 to V<sub>CC(min)</sub> and 200 μs wait time after V<sub>CC</sub> stabilization.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = V<sub>CC(typ)</sub>, T<sub>A</sub> = 25 °C.
- Please note that the maximum V<sub>OH</sub> limit does not exceed minimum CMOS V<sub>IH</sub> of 3.5 V. If you are interfacing this SRAM with 5 V legacy processors that require a minimum V<sub>IH</sub> of 3.5 V, please refer to Application Note AN6081 for technical details and options you may consider.
- Chip enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the I<sub>SB1</sub> / I<sub>SB2</sub> / I<sub>CCDR</sub> spec. Other inputs can be left floating.

## Capacitance

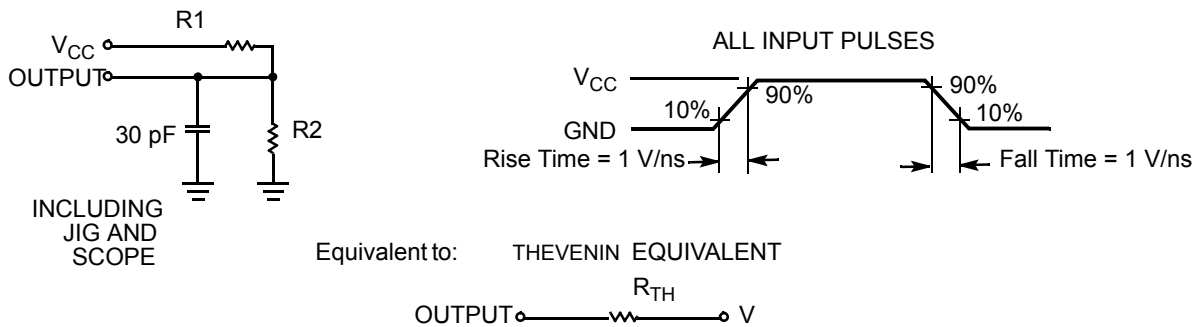
Parameter <sup>[10]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = V <sub>CC(typ)</sub>	10	pF
C <sub>OUT</sub>	Output capacitance		10	pF

## Thermal Resistance

Parameter <sup>[10]</sup>	Description	Test Conditions	44-pin TSOP II	Unit
Θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, two-layer printed circuit board	28.2	°C/W
Θ <sub>JC</sub>	Thermal resistance (junction to case)		3.4	°C/W

## AC Test Loads and Waveforms

Figure 1. AC Test Loads and Waveforms



Parameters	2.50 V	3.0 V	5.0 V	Unit
R1	16600	1103	1800	Ω
R2	15400	1554	990	Ω
R <sub>TH</sub>	8000	645	639	Ω
V <sub>TH</sub>	1.2	1.75	1.77	V

### Note

10. Tested initially and after any design or process changes that may affect these parameters.

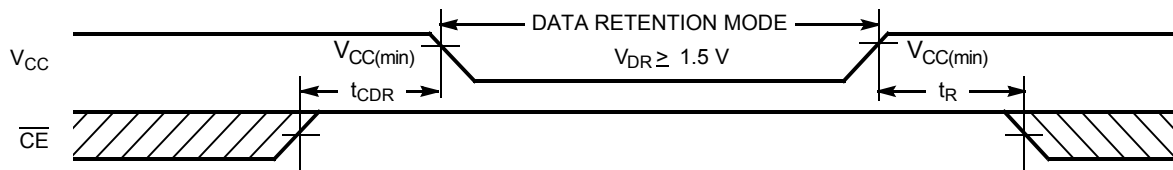
## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Typ <sup>[11]</sup>	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention		1.5	–	–	V
$I_{CCDR}$ <sup>[12]</sup>	Data retention current	$\overline{CE} \geq V_{CC} - 0.2\text{ V}$ , $V_{IN} \geq V_{CC} - 0.2\text{ V}$ or $V_{IN} \leq 0.2\text{ V}$	–	–	3	$\mu\text{A}$
$t_{CDR}$ <sup>[13]</sup>	Chip deselect to data retention time		0	–	–	ns
$t_R$ <sup>[14]</sup>	Operation recovery time		45	–	–	ns

## Data Retention Waveform

Figure 2. Data Retention Waveform



### Notes

11. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at  $V_{CC} = V_{CC(typ)}$ ,  $T_A = 25\text{ }^\circ\text{C}$ .
12. Chip enable ( $\overline{CE}$ ) must be HIGH at CMOS level to meet the  $I_{SB1} / I_{SB2} / I_{CCDR}$  spec. Other inputs can be left floating.
13. Tested initially and after any design or process changes that may affect these parameters.
14. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$  or stable at  $V_{CC(min)} \geq 100\text{ }\mu\text{s}$ .

## Switching Characteristics

Over the Operating Range

Parameter <sup>[15]</sup>	Description	45 ns		Unit
		Min	Max	
<b>Read Cycle</b>				
t <sub>RC</sub>	Read cycle time	45	–	ns
t <sub>AA</sub>	Address to data valid	–	45	ns
t <sub>OHA</sub>	Data hold from address change	10	–	ns
t <sub>ACE</sub>	$\overline{CE}$ LOW to data valid	–	45	ns
t <sub>DOE</sub>	$\overline{OE}$ LOW to data valid	–	22	ns
t <sub>LZOE</sub>	$\overline{OE}$ LOW to Low Z <sup>[16]</sup>	5	–	ns
t <sub>HZOE</sub>	$\overline{OE}$ HIGH to High Z <sup>[16, 17]</sup>	–	18	ns
t <sub>LZCE</sub>	$\overline{CE}$ LOW to Low Z <sup>[16]</sup>	10	–	ns
t <sub>HZCE</sub>	$\overline{CE}$ HIGH to High Z <sup>[16, 17]</sup>	–	18	ns
t <sub>PU</sub>	$\overline{CE}$ LOW to power up	0	–	ns
t <sub>PD</sub>	$\overline{CE}$ HIGH to power up	–	45	ns
t <sub>DBE</sub>	$\overline{BHE}$ / $\overline{BLE}$ LOW to data valid	–	22	ns
t <sub>LZBE</sub>	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low Z <sup>[16]</sup>	5	–	ns
t <sub>HZBE</sub>	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High Z <sup>[16, 17]</sup>	–	18	ns
<b>Write Cycle <sup>[18]</sup></b>				
t <sub>WC</sub>	Write cycle time	45	–	ns
t <sub>SCE</sub>	$\overline{CE}$ LOW to write end	35	–	ns
t <sub>AW</sub>	Address setup to write end	35	–	ns
t <sub>HA</sub>	Address Hold from write end	0	–	ns
t <sub>SA</sub>	Address setup to write start	0	–	ns
t <sub>PWE</sub>	$\overline{WE}$ pulse width	35	–	ns
t <sub>BW</sub>	$\overline{BHE}$ / $\overline{BLE}$ pulse width	35	–	ns
t <sub>SD</sub>	Data setup to write end	25	–	ns
t <sub>HD</sub>	Data hold from write end	0	–	ns
t <sub>HZWE</sub>	$\overline{WE}$ LOW to High Z <sup>[16, 17]</sup>	–	18	ns
t <sub>LZWE</sub>	$\overline{WE}$ HIGH to Low Z <sup>[16]</sup>	10	–	ns

### Notes

15. Test Conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less (1 V/ns), timing reference levels of  $V_{CC(typ)}/2$ , input pulse levels of 0 to  $V_{CC(typ)}$ , and output loading of the specified  $I_{OL}/I_{OH}$  as shown in the [Figure 1 on page 5](#).
16. At any given temperature and voltage condition, t<sub>HZCE</sub> is less than t<sub>LZCE</sub>, t<sub>HZBE</sub> is less than t<sub>LZBE</sub>, t<sub>HZOE</sub> is less than t<sub>LZOE</sub>, and t<sub>HZWE</sub> is less than t<sub>LZWE</sub> for any given device.
17. t<sub>HZOE</sub>, t<sub>HZCE</sub>, t<sub>HZBE</sub>, and t<sub>HZWE</sub> transitions are measured when the output enter a high impedance state.
18. The internal write time of the memory is defined by the overlap of  $\overline{WE}$ ,  $\overline{CE} = V_{IL}$ . All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must be referenced to the edge of the signal that terminates the write.

### Switching Waveforms

Figure 3. Read Cycle No. 1 (Address Transition Controlled) [19, 20]

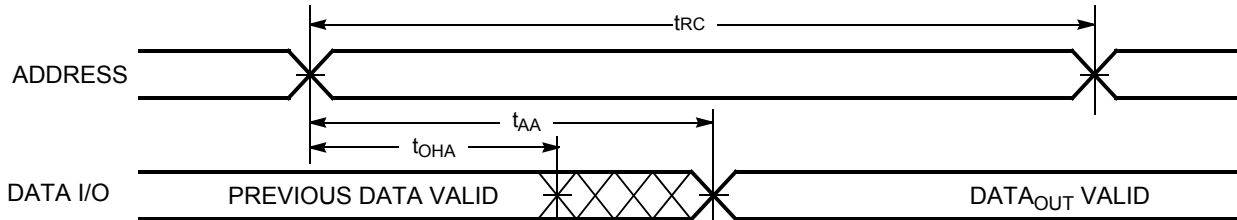
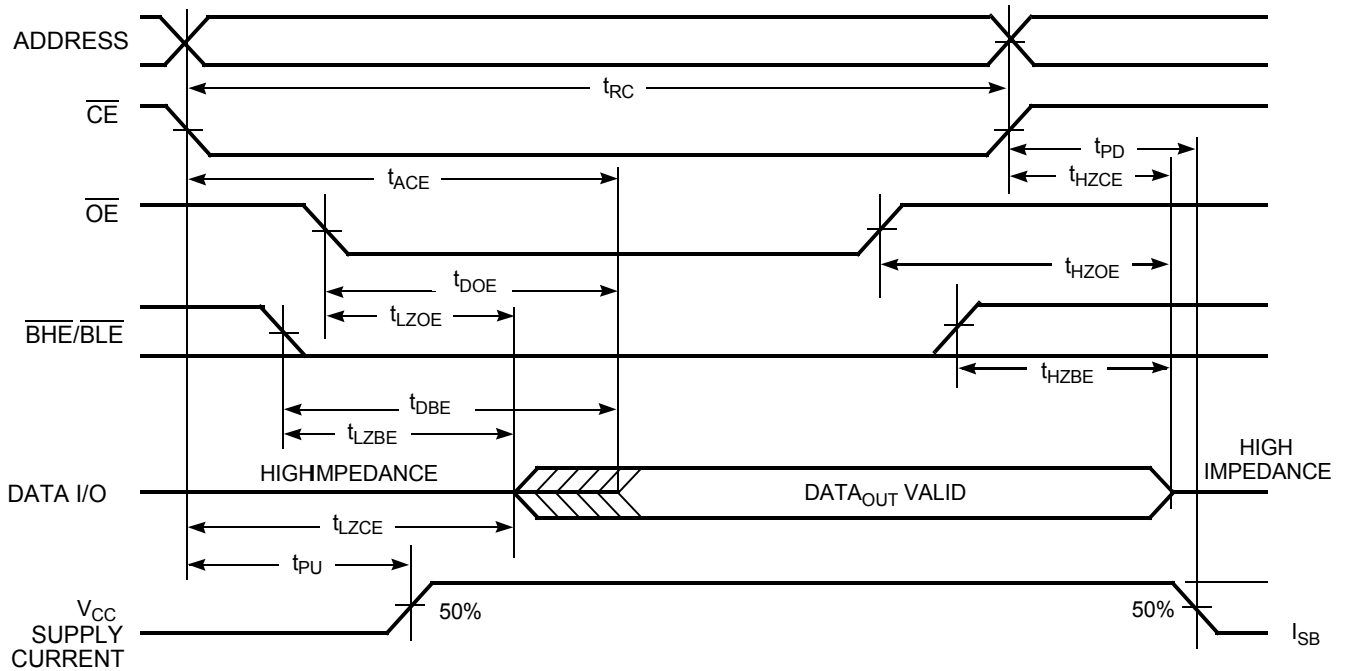


Figure 4. Read Cycle No. 2 ( $\overline{\text{OE}}$  Controlled) [20, 21]



**Notes**

- 19. Device is continuously selected.  $\overline{\text{OE}}, \overline{\text{CE}} = V_{IL}$ .
- 20.  $\overline{\text{WE}}$  is high for read cycles.
- 21. Address valid before or similar to  $\overline{\text{CE}}$  transition low.



Switching Waveforms (continued)

Figure 5. Write Cycle No. 1 ( $\overline{WE}$  Controlled,  $\overline{OE}$  HIGH during Write) [22, 23]

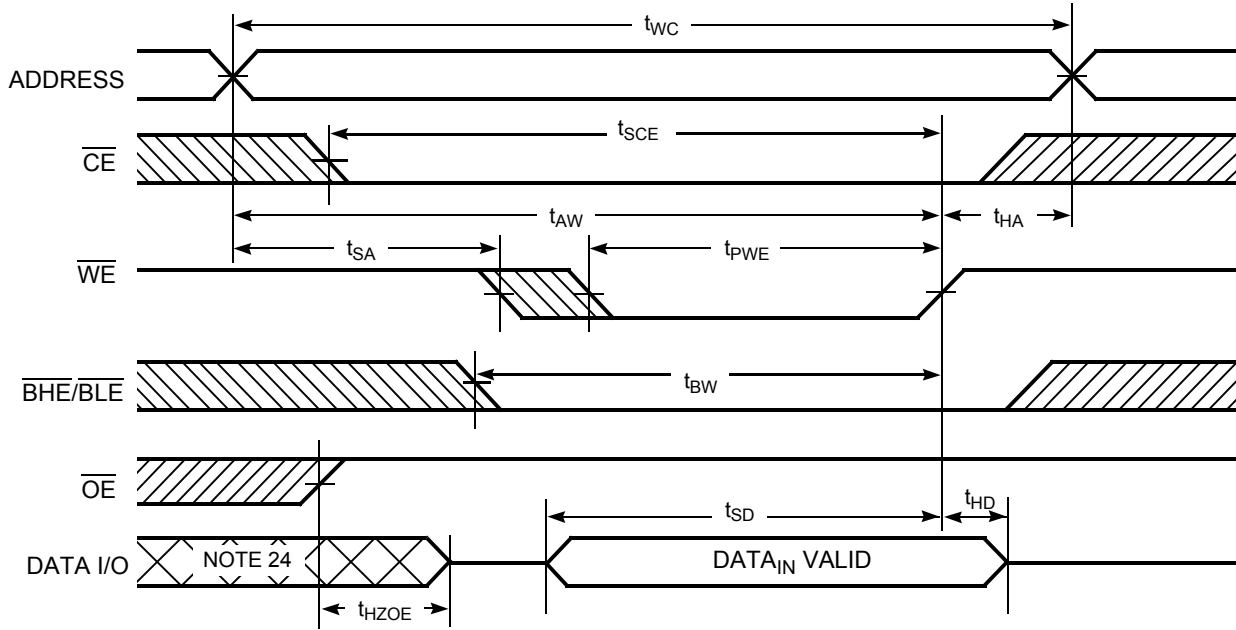
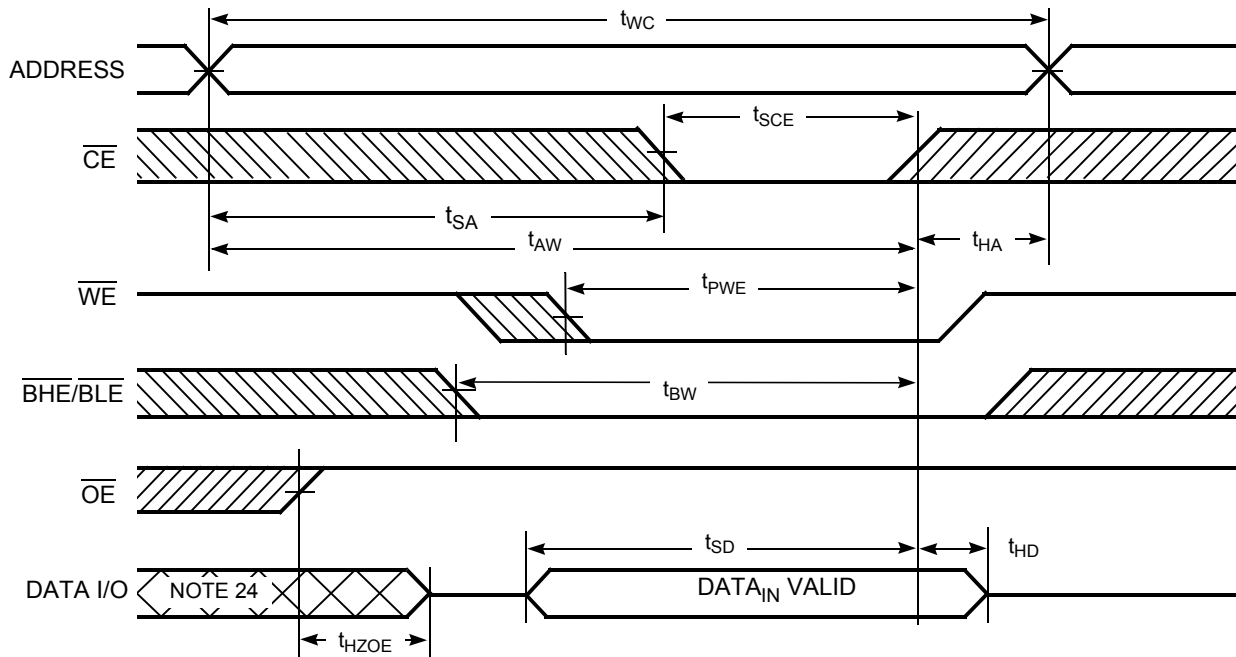


Figure 6. Write Cycle No. 2 ( $\overline{CE}$  Controlled) [22, 23]



Notes

- 22. Data I/O is high impedance if  $\overline{OE} = V_{IH}$ .
- 23. If  $\overline{CE}$  goes high simultaneously with  $\overline{WE}$  high, the output remains in high impedance state.
- 24. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms (continued)

Figure 7. Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) [25]

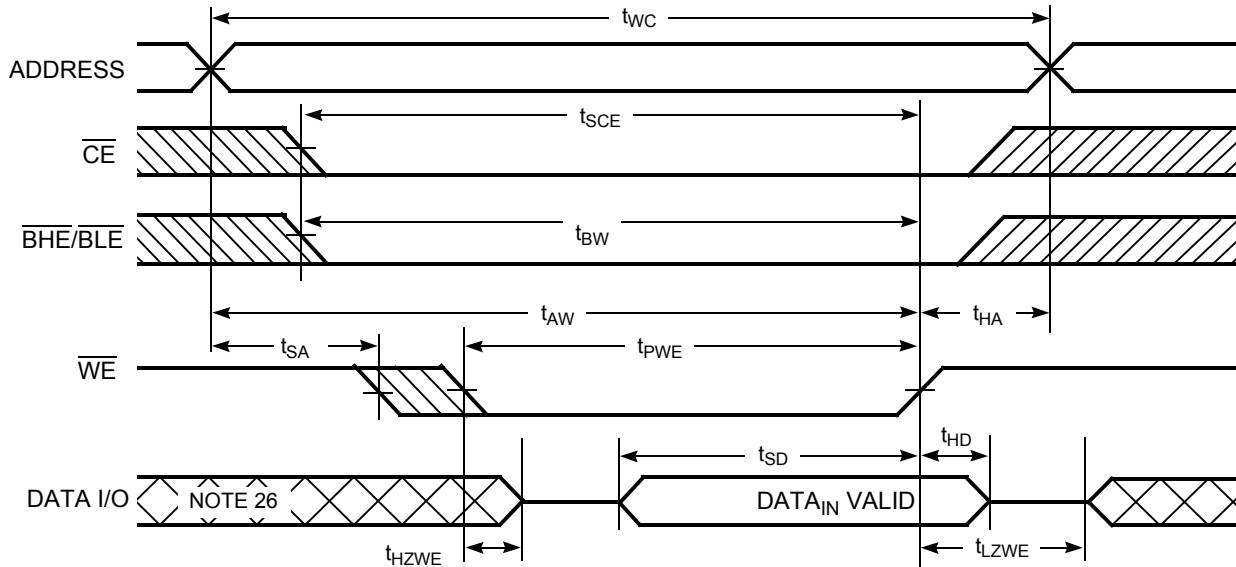
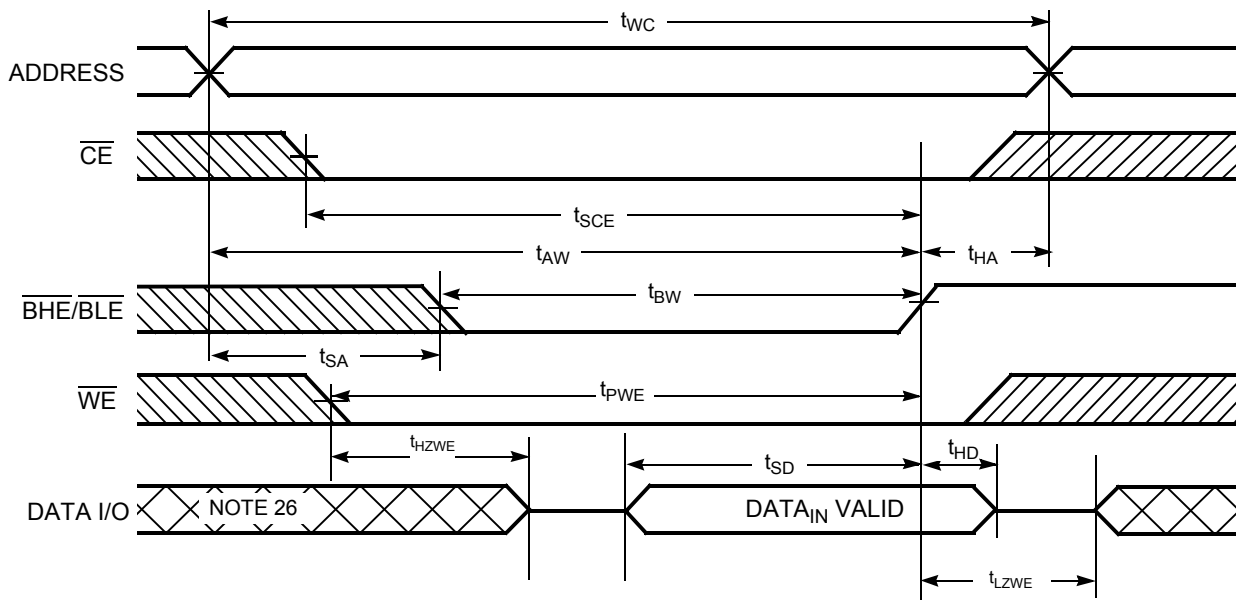


Figure 8. Write Cycle No. 4 ( $\overline{BHE/BLE}$  Controlled,  $\overline{OE}$  LOW) [25]



Notes

- 25. If  $\overline{CE}$  goes high simultaneously with  $\overline{WE}$  high, the output remains in high impedance state.
- 26. During this period, the I/Os are in output state. Do not apply input signals.

**Truth Table**

$\overline{CE}^{[27]}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect or power down	Standby ( $I_{SB}$ )
L	X	X	H	H	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	L	L	L	Data out ( $I/O_0$ – $I/O_{15}$ )	Read	Active ( $I_{CC}$ )
L	H	L	H	L	Data out ( $I/O_0$ – $I/O_7$ ); $I/O_8$ – $I/O_{15}$ in High Z	Read	Active ( $I_{CC}$ )
L	H	L	L	H	Data Out ( $I/O_8$ – $I/O_{15}$ ); $I/O_0$ – $I/O_7$ in High Z	Read	Active ( $I_{CC}$ )
L	H	H	L	L	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	H	H	L	High Z	Output disabled	Active ( $I_{CC}$ )
L	H	H	L	H	High Z	Output disabled	Active ( $I_{CC}$ )
L	L	X	L	L	Data in ( $I/O_0$ – $I/O_{15}$ )	Write	Active ( $I_{CC}$ )
L	L	X	H	L	Data in ( $I/O_0$ – $I/O_7$ ); $I/O_8$ – $I/O_{15}$ in High Z	Write	Active ( $I_{CC}$ )
L	L	X	L	H	Data in ( $I/O_8$ – $I/O_{15}$ ); $I/O_0$ – $I/O_7$ in High Z	Write	Active ( $I_{CC}$ )

**Note**

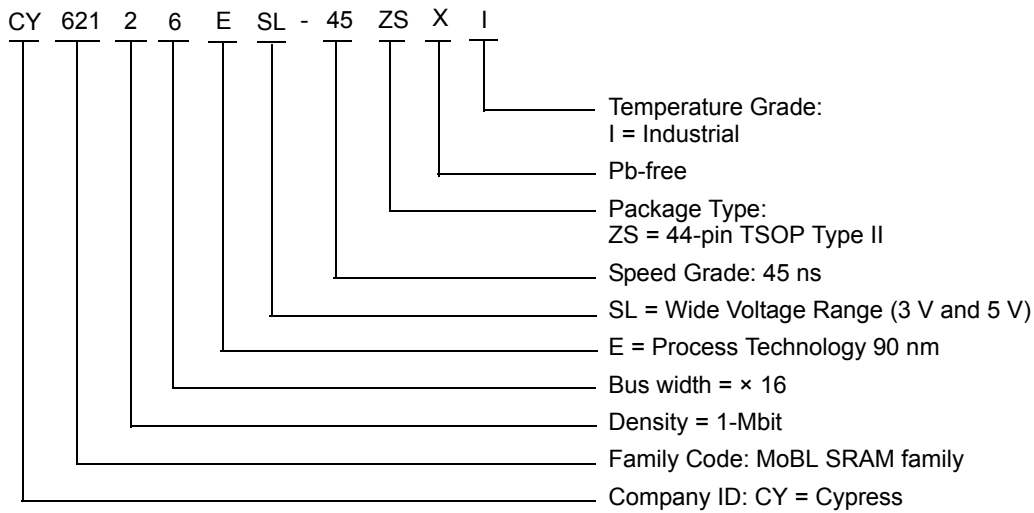
27. Chip enable must be at CMOS levels (not floating). Intermediate voltage levels on this pin is not permitted.

### Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62126ESL-45ZSXI	51-85087	44-pin TSOP II (Pb-free)	Industrial

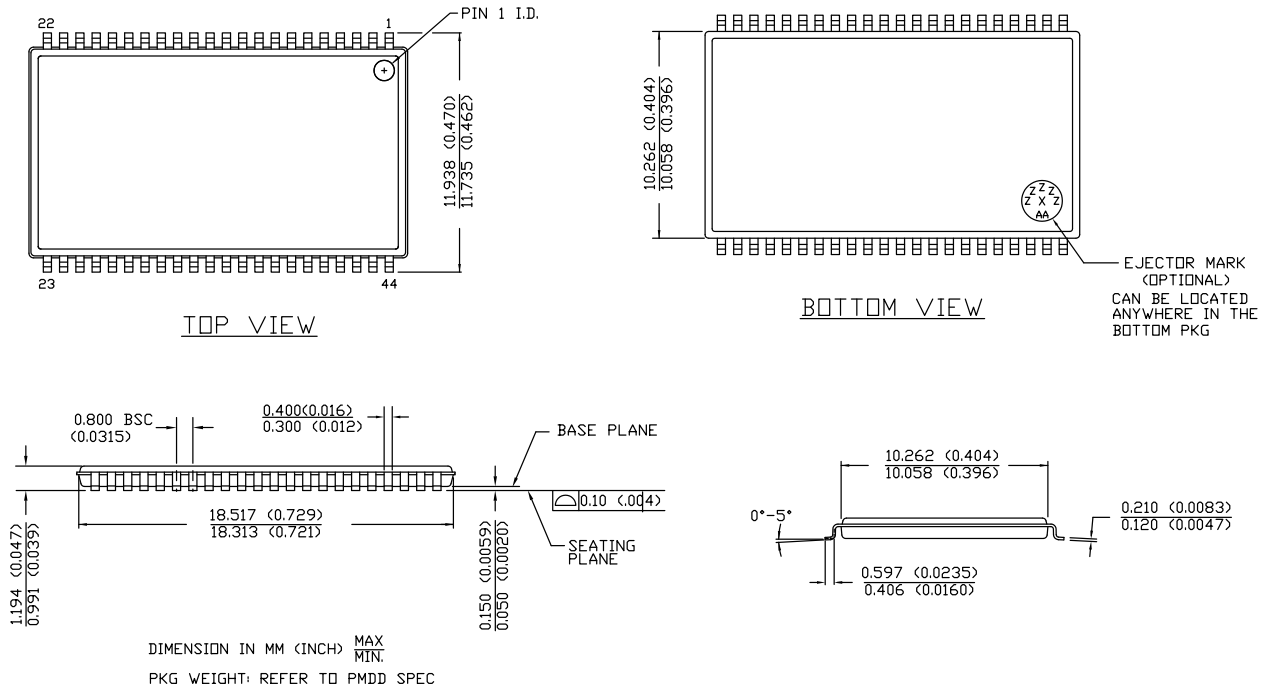
Contact your local Cypress sales representative for availability of these parts.

### Ordering Code Definitions



Package Diagram

Figure 9. 44-pin TSOP Z44-II Package Outline, 51-85087



51-85087 \*E

## Acronyms

Acronym	Description
$\overline{\text{BHE}}$	Byte High Enable
$\overline{\text{BLE}}$	Byte Low Enable
$\overline{\text{CE}}$	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
$\overline{\text{OE}}$	Output Enable
SRAM	Static Random Access Memory
TSOP	Thin Small Outline Package
$\overline{\text{WE}}$	Write Enable

## Document Conventions

### Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

**Document History Page**

Document Title: CY62126ESL MoBL <sup>®</sup> , 1-Mbit (64 K × 16) Static RAM				
Document Number: 001-45076				
Revision	ECN	Submission Date	Orig. of Change	Description of Change
**	2610988	11/21/08	VKN / PYRS	New data sheet.
*A	2718906	06/15/2009	VKN	Post to external web
*B	2944332	06/04/2010	VKN	Added <a href="#">Contents</a> Updated <a href="#">Electrical Characteristics</a> (Added Note 9 and referred the same note in I <sub>SB2</sub> parameter). Updated <a href="#">Truth Table</a> (Added Note 27 and referred the same note in $\overline{CE}$ column). Updated <a href="#">Package Diagram</a> . Updated links in <a href="#">Sales, Solutions, and Legal Information</a> .
*C	3113720	12/17/2010	PRAS	Added <a href="#">Ordering Code Definitions</a> .
*D	3292276	06/24/2011	RAME	Updated <a href="#">Functional Description</a> (Removed "For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines."). Updated <a href="#">Data Retention Characteristics</a> (Changed the minimum value of t <sub>R</sub> parameter). Updated in new template.
*E	3503697	01/20/2012	TAVA	Updated <a href="#">Electrical Characteristics</a> (Replaced V <sub>I</sub> with V <sub>IN</sub> in Test Conditions of I <sub>X</sub> parameter). Updated <a href="#">Switching Waveforms</a> . Updated <a href="#">Package Diagram</a> .
*F	4013949	06/04/2013	MEMJ	Updated <a href="#">Functional Description</a> .  Updated <a href="#">Electrical Characteristics</a> : Added one more Test Condition "4.5 ≤ V <sub>CC</sub> ≤ 5.5, I <sub>OH</sub> = -0.1 mA" for V <sub>OH</sub> parameter and added maximum value corresponding to that Test Condition. Added Note 8 and referred the same note in maximum value for V <sub>OH</sub> parameter corresponding to Test Condition "4.5 ≤ V <sub>CC</sub> ≤ 5.5, I <sub>OH</sub> = -0.1 mA".  Updated <a href="#">Package Diagram</a> : spec 51-85087 – Changed revision from *D to *E.

## Sales, Solutions, and Legal Information

### Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at [Cypress Locations](#).

### Products

Automotive	<a href="http://cypress.com/go/automotive">cypress.com/go/automotive</a>
Clocks & Buffers	<a href="http://cypress.com/go/clocks">cypress.com/go/clocks</a>
Interface	<a href="http://cypress.com/go/interface">cypress.com/go/interface</a>
Lighting & Power Control	<a href="http://cypress.com/go/powerpsoc">cypress.com/go/powerpsoc</a> <a href="http://cypress.com/go/plc">cypress.com/go/plc</a>
Memory	<a href="http://cypress.com/go/memory">cypress.com/go/memory</a>
Optical & Image Sensing	<a href="http://cypress.com/go/image">cypress.com/go/image</a>
PSoC	<a href="http://cypress.com/go/psoc">cypress.com/go/psoc</a>
Touch Sensing	<a href="http://cypress.com/go/touch">cypress.com/go/touch</a>
USB Controllers	<a href="http://cypress.com/go/USB">cypress.com/go/USB</a>
Wireless/RF	<a href="http://cypress.com/go/wireless">cypress.com/go/wireless</a>

### PSoC Solutions

[psoc.cypress.com/solutions](http://psoc.cypress.com/solutions)  
PSoC 1 | PSoC 3 | PSoC 5

---

© Cypress Semiconductor Corporation, 2008-2013. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress product. Nor does it convey or imply any license under patent or other rights. Cypress products are not warranted nor intended to be used for medical, life support, life saving, critical control or safety applications, unless pursuant to an express written agreement with Cypress. Furthermore, Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress products in life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Any Source Code (software and/or firmware) is owned by Cypress Semiconductor Corporation (Cypress) and is protected by and subject to worldwide patent protection (United States and foreign), United States copyright laws and international treaty provisions. Cypress hereby grants to licensee a personal, non-exclusive, non-transferable license to copy, use, modify, create derivative works of, and compile the Cypress Source Code and derivative works for the sole purpose of creating custom software and or firmware in support of licensee product to be used only in conjunction with a Cypress integrated circuit as specified in the applicable agreement. Any reproduction, modification, translation, compilation, or representation of this Source Code except as specified above is prohibited without the express written permission of Cypress.

Disclaimer: CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS MATERIAL, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. Cypress reserves the right to make changes without further notice to the materials described herein. Cypress does not assume any liability arising out of the application or use of any product or circuit described herein. Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress' product in a life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Use may be limited by and subject to the applicable Cypress software license agreement.